



520.36911CX2

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): T. ONO, et al

Serial No.: 09/249,292

Filed: February 12, 1999

For: METHOD AND APPARATUS FOR TREATING SURFACE OF SEMICONDUCTOR

Group: 1763

Examiner: A. Olsen

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AMENDMENT

Mail Stop Non-Fee Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

June 11, 2003

Sir:

The following amendments and remarks are respectfully submitted in connection with the above-identified application in response to the Office Action dated March 11, 2003.

IN THE CLAIMS:

Please amend claim 1 as follows:

1. (four times amended) A method of treating a surface of a sample, comprising the steps of:
- generating a plasma in a treatment chamber;
 - applying an rf bias voltage of a frequency of at least 100 kHz so that ions of intermediate energy which promote etching reaction while providing poor directionality are reduced, and ions of high energy having a high directionality and ions of low energy which do not contribute to etching are increased, so as to have at least one peak point at a region of high ion energy and at least one peak point at a

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